

**SOT-23 Plastic-Encapsulate Transistors****M8550** TRANSISTOR (PNP)**FEATURES**

Power dissipation

 P_{CM} : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

 I_{CM} : -1 A

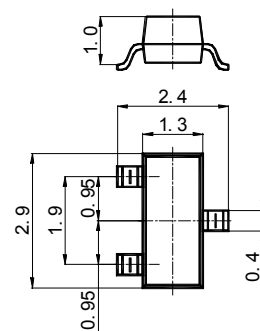
Collector-base voltage

 $V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **SOT-23**

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -5mA$	45		
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -100mA$	85	300	
	$h_{FE\ominus3\boxtimes}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

* Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.